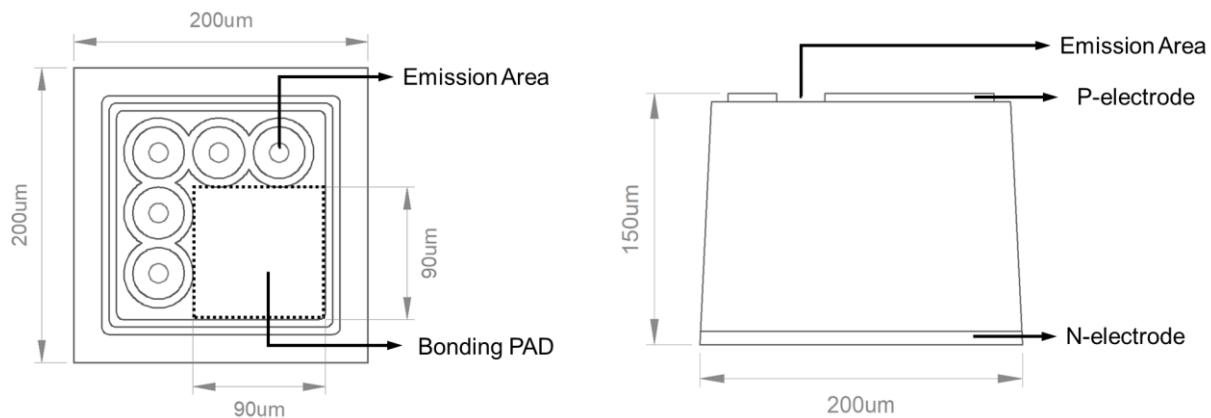


■ Features & Applications :

- 650 nm Wavelength
- Multi-emitters

■ Outline Dimensions : (Unit: um)



■ Physical Structure :

Chip dimension	Chip size	200um x 200um
	Bonding Pad	90um x 90um
	Thickness	150 ± 20 um
Electrode	N (cathode)	Gold
	P (anode)	Gold

■ Electro-Optical Characteristics :

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Output Power	Po	IF = 15 mA	5	6.5	--	mW
Forward Voltage	VF	IF = 15 mA	--	2.4	--	V
Threshold Current	Ith	--	--	5.0	--	mA
Wavelength	λ_p	IF = 15 mA	640	650	660	nm
Beam Divergence (1/e2)	θ	IF = 15 mA	--	18.0	--	degree

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

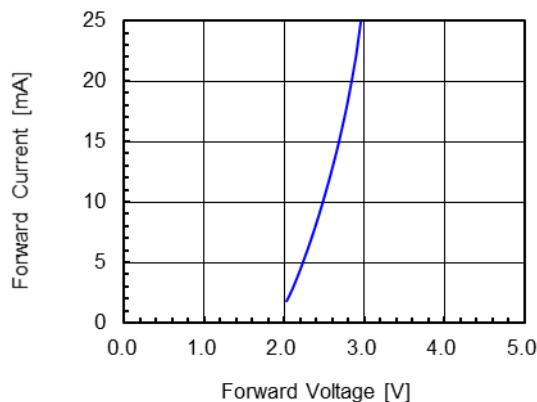


Fig 2. Relative Radiant Power vs Wavelength

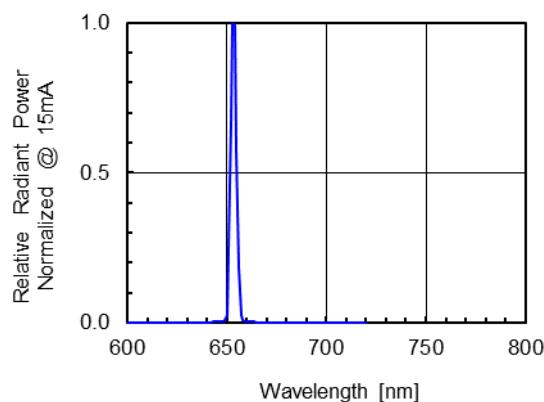


Fig 3. Relative Radiant Power

vs. Forward DC Current

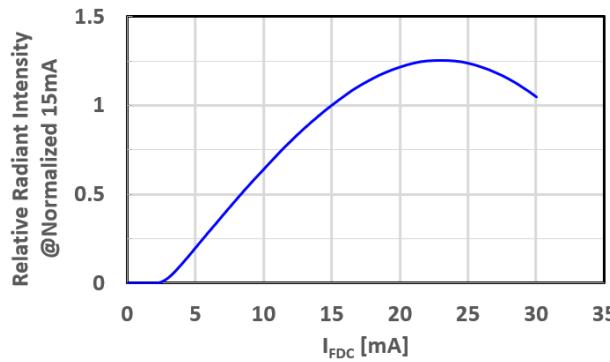
Relative Radiant Power vs.
DC Forward Current

Fig 4. Relative Radiant Power

vs. emission angle

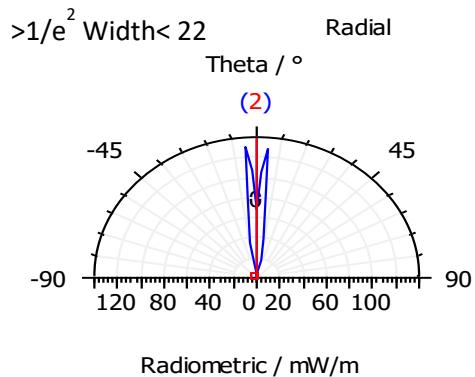


Fig 5. Forward DC Voltage vs. Temperature

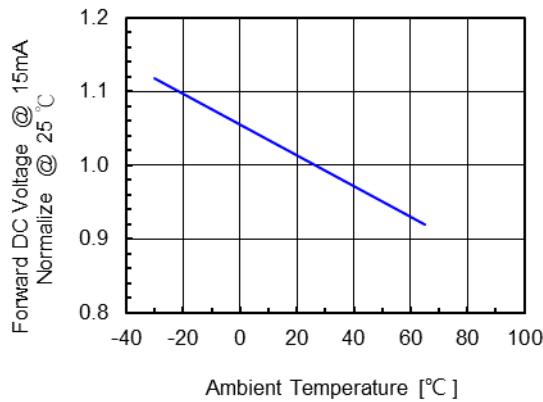


Fig 6. Relative Radiant Power vs. Temperature

